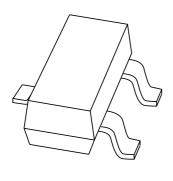
DISCRETE SEMICONDUCTORS

DATA SHEET



BAT754 seriesSchottky barrier (double) diodes

Product specification
Supersedes data of 1999 Aug 05

2003 Mar 25





Schottky barrier (double) diodes

BAT754 series

FEATURES

- · Very low forward voltage
- · Guard ring protected
- Small plastic SMD package
- Low diode capacitance.

APPLICATIONS

- Ultra high-speed switching
- · Voltage clamping
- · Protection circuits
- · Blocking diodes
- Low power consumption applications, e.g. hand-held applications.

DESCRIPTION

Planar Schottky barrier diodes encapsulated in a SOT23 small plastic SMD package. Low forward voltage selection of the BAT54 series. Single diodes and double diodes with different pinning are available.

PINNING

PIN	BAT754					
FIN		Α	С	S		
1	а	k ₁	a ₁	a ₁		
2	n.c.	k ₂	a ₂	k ₂		
3	k	a ₁ , a ₂	k ₁ , k ₂	k ₁ , a ₂		

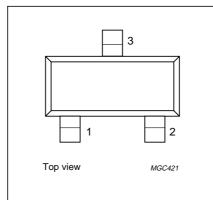


Fig.1 Simplified outline (SOT23) and pin configuration.

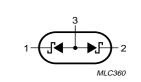


Fig.3 BAT754A diode configuration (symbol).

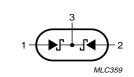


Fig.4 BAT754C diode configuration (symbol).

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾	
BAT754	2K*	
BAT754A	2L*	
BAT754C	2M*	
BAT754S	2N*	

Note

1. * = p: Made in Hong Kong.

* = t : Made in Malaysia.* = W : Made in China.

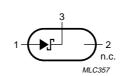


Fig.2 BAT754 single diode configuration (symbol).

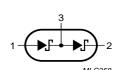


Fig.5 BAT754S diode configuration (symbol).

Schottky barrier (double) diodes

BAT754 series

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per diode							
V _R	continuous reverse voltage		_	30	V		
I _F	continuous forward current		_	200	mA		
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	_	300	mA		
I _{FSM}	non-repetitive peak forward current	t = 8.3 ms half sinewave; JEDEC method	_	600	mA		
T _{stg}	storage temperature		-65	+150	°C		
Tj	junction temperature		_	125	°C		
T _{amb}	operating ambient temperature		-65	+125	°C		

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V _F	forward voltage	see Fig.6			
		I _F = 0.1 mA	_	200	mV
		I _F = 1 mA	_	260	mV
		I _F = 10 mA	_	340	mV
		I _F = 30 mA	_	420	mV
		I _F = 100 mA	600	_	mV
I _R	reverse current	V _R = 25 V; note 1; see Fig.7	_	2	μΑ
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; see Fig.8	_	10	pF

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

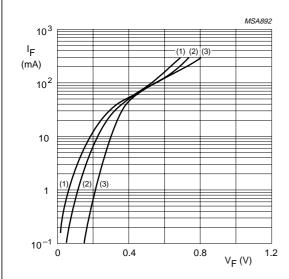
1. Refer to SOT23 standard mounting conditions.

^{1.} Pulse test: t_p = 300 μ s; $\delta \le$ 0.02.

Schottky barrier (double) diodes

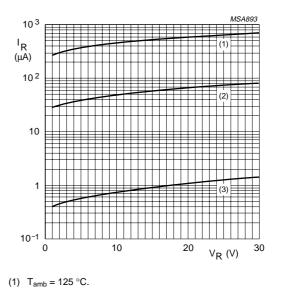
BAT754 series

GRAPHICAL DATA



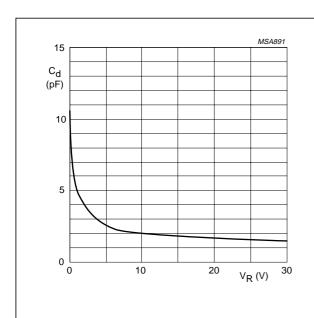
- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.6 Forward current as a function of forward voltage; typical values.



- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.

Fig.7 Reverse current as a function of reverse voltage; typical values.



 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}.$

Fig.8 Diode capacitance as a function of reverse voltage; typical values.

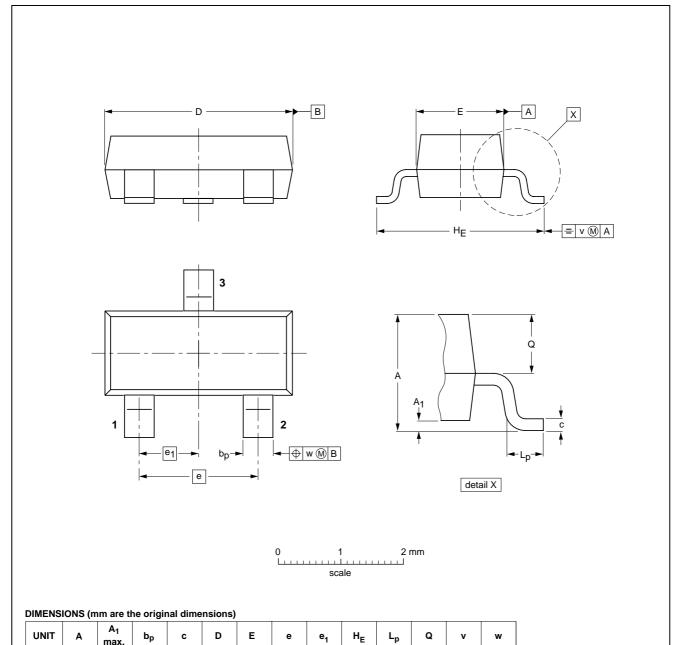
Schottky barrier (double) diodes

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT23		TO-236AB			97-02-28 99-09-13

1.9

0.45

0.55

0.1

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max.

0.48

0.15

1.1

Schottky barrier (double) diodes

BAT754 series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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BAT754 series

NOTES

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